ABSTRACT

A semiconductor device may include a substrate including a first and a second row region, wherein a surface of the substrate is disposed in a first direction and a second direction perpendicular to the first direction, a first nanosheet structure on the first row region and including active segments disposed in the first direction, and the active segments having different widths in the second direction; and a second nanosheet structure on the second row region, the second nanosheet structure spaced apart from the first nanosheet structure in the second direction, and wherein the second nanosheet structure is symmetrical to the first nanosheet structure in the first direction. In a plan view, in each of the first and second nanosheet structures, transition regions between adjacent ones of the active segments have one of a same first angle and a second angle with respect to the first direction.

FIG. 2